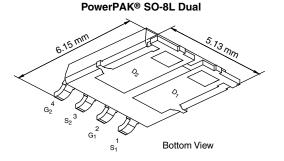
SQJ968EP



Vishay Siliconix

Automotive Dual N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	60					
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0336					
$R_{DS(on)} (\Omega)$ at $V_{GS} = 4.5 V$	0.0444					
I _D (A) per leg	18					
Configuration	Dual					

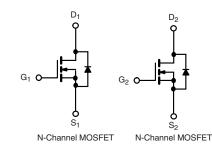


FEATURES

- TrenchFET® Power MOSFET
- AEC-Q101 Qualified
- 100 % R_g and UIS Tested
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>



RoHS COMPLIANT HALOGEN FREE



ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and Halogen-free	SQJ968EP-T1-GE3

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	60		
Gate-Source Voltage	V _{GS}	± 20	V		
Continuous Drain Current ^a	T _C = 25 °C		18		
Continuous Drain Currenta	T _C = 125 °C	I _D	10.5		
Continuous Source Current (Diode Conduct	ion) ^a	I _S	23	А	
Pulsed Drain Current ^b		I _{DM}	72		
Single Pulse Avalanche Current		I _{AS}	9		
Single Pulse Avalanche Energy L = 0.1 mH		E _{AS}	4	mJ	
Mauine Davie Diasinationh	T _C = 25 °C	6	25	14/	
Maximum Power Dissipation ^b	T _C = 125 °C	PD	8	W	
Operating Junction and Storage Temperatu	re Range	T _J , T _{stg}	- 55 to + 175		
Soldering Recommendations (Peak Temper		260	°C		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	85	°C/W
Junction-to-Case (Drain)		R _{thJC}	6	0/10

Notes

c. When mounted on 1" square PCB (FR4 material).

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

1

a. Package limited.

b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static					•		
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} =	= 0 V, I _D = 250 μA	60	-	-	v
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$		2.0	2.5	v
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 20$ V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 175 °C	-	-	150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α
		V _{GS} = 10 V	I _D = 4.8 A	-	0.0280	0.0336	Ω
Drain-Source On-State Resistance ^a	Р	V _{GS} = 10 V	I _D = 4.8 A, T _J = 125 °C	-	-	0.0900	
	R _{DS(on)}	V _{GS} = 10 V	I _D = 4.8 A, T _J = 175 °C	-	-	0.1430	
		$V_{GS} = 4.5 V$	I _D = 4.2 A	-	0.0370	0.0444	
Forward Transconductanceb	9 _{fs}	V _{DS} :	= 15 V, I _D = 4.8 A	-	16	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	571	714	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 30 V, f = 1 MHz	-	98	123	pF
Reverse Transfer Capacitance	C _{rss}			-	38	48	1
Total Gate Charge ^c	Qg			-	12.3	18.5	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 30 \text{ V}, \text{ I}_{D} = 4.5 \text{ A}$	-	1.9	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	2.6	-	1
Gate Resistance	R _g		f = 1 MHz	2	3.94	6	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	8	12	
Rise Time ^c	t _r	$\label{eq:VDD} \begin{array}{l} V_{DD} = 30 \text{ V}, \text{ R}_L = 30 \ \Omega \\ I_D \cong 1 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \ \Omega \end{array}$		-	9	13.5	- ns
Turn-Off Delay Time ^c	t _{d(off)}			-	19.5	29	
Fall Time ^c	t _f			-	6.5	10	
Source-Drain Diode Ratings and Char	acteristics ^b	•		•		•	
Pulsed Current ^a	I _{SM}			-	-	32	Α
		$I_{\rm F} = 3.1 \text{A}, V_{\rm GS} = 0 \text{V}$					

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

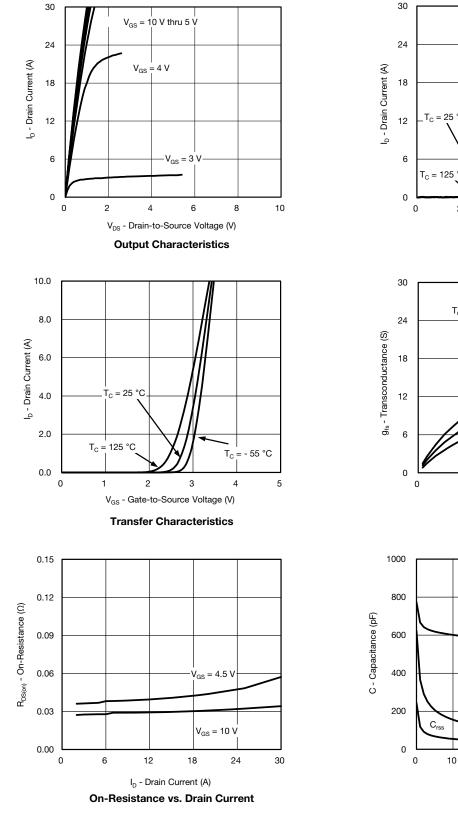
c. Independent of operating temperature.

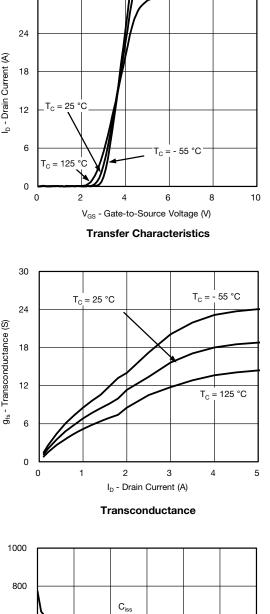
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)







30

40

50

20

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3

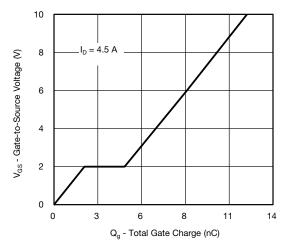
Document Number: 62817

60

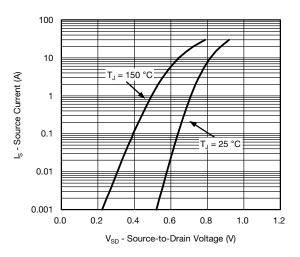
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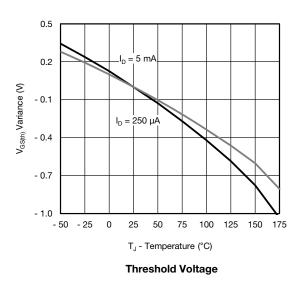
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)

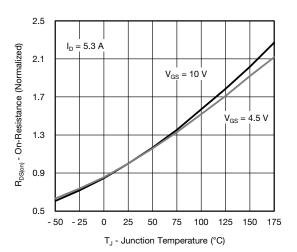


Gate Charge

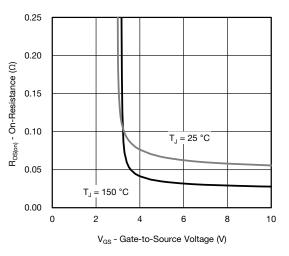


Source Drain Diode Forward Voltage

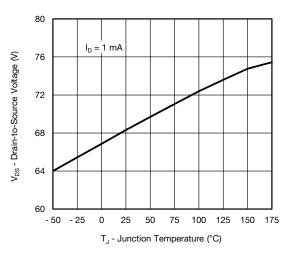




On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

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4

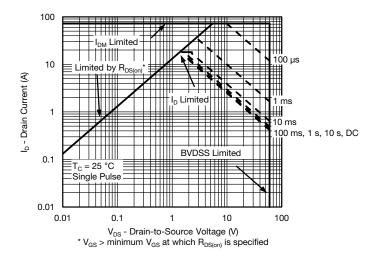
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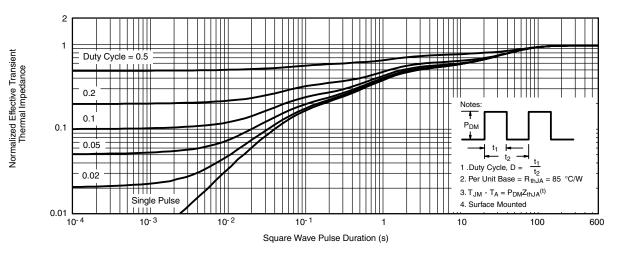
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Safe Operating Area



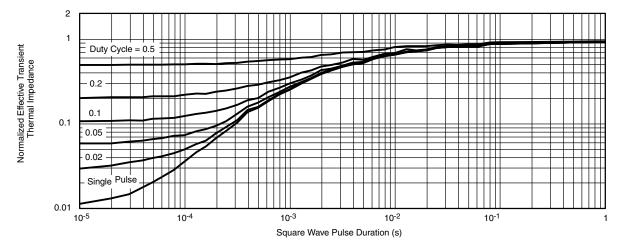
Normalized Thermal Transient Impedance, Junction-to-Ambient



SQJ968EP

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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

The characteristics shown in the two graphs

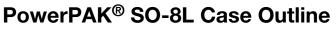
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

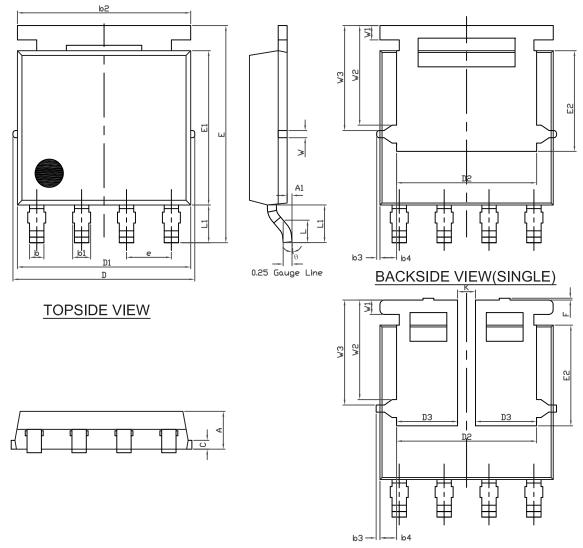
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62817.







BACKSIDE VIEW(DUAL)

Package Information



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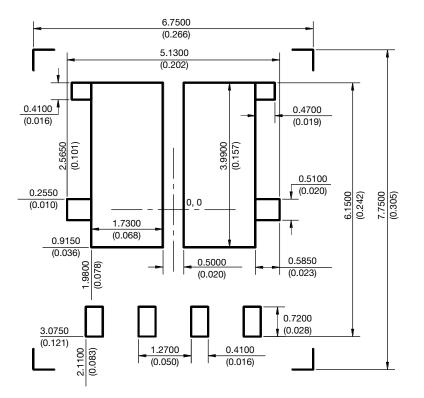
DIM.		MILLIMETERS		INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094	·	0.004			
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC	·	0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2 (for AI product)	2.75	2.85	2.95	0.108	0.112	0.116	
E2 (for other product)	3.18	3.28	3.38	0.125	0.129	0.133	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
К		0.51		0.020			
W	0.23		0.009				
W1	0.41		0.016				
W2	2.82		0.111				
W3		2.96		0.117			
θ	0°	-	10°	0°	-	10°	

Note

• Millimeters will gover



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L DUAL



Recommended Minimum Pads Dimensions in mm (inches) Keep-out 6.75 (0.266) x 7.75 (0.305)

Revision: 07-Feb-12



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